





#### N-CHANNEL ENHANCEMENT MODE MOSFET

#### **Features**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Low Gate Resistance
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

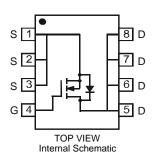
#### **Mechanical Data**

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.072 grams (approximate)

SO-8



TOP VIEW



## Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 3)	Steady State	T <sub>A</sub> = 25°C T <sub>A</sub> = 85°C	I <sub>D</sub>	10 6	А
Pulsed Drain Current (Note 4)			I <sub>DM</sub>	60	Α
Avalanche Current (Notes 4 & 5)		I <sub>AR</sub>	16	A	
Repetitive Avalanche Energy (Notes 4 & 5) L = 0.1mH		E <sub>AR</sub>	12.8	mJ	

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	$P_{D}$	1.42	W
Thermal Resistance, Junction to Ambient @Ta = 25°C (Note 3)	$R_{\theta JA}$	88.4	°C/W
Operating and Storage Temperature Range	$T_J$ , $T_{STG}$	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.
   Device mounted on FR-4 substrate PC board with minimum recommended pad layout in a still air environment @ T<sub>A</sub> = 25°C. The value in any given application depends on the user's specific board design.

  4. Repetitive rating, pulse width limited by junction temperature.
- 5.  $I_{AR}$  and  $E_{AR}$  rating are based on low frequency and duty cycles to keep  $T_J$  = 25°C

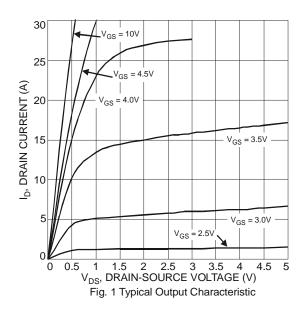


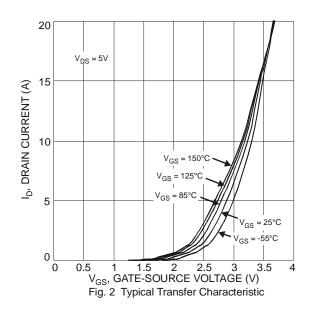
### **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	-	-	1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	1	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	$V_{GS(th)}$	1.0	1.45	2.4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance		-	15 25	23 33	mΩ	$V_{GS} = 10V, I_D = 10A$	
Static Dialii-Source Off-Resistance	R <sub>DS</sub> (ON)					$V_{GS} = 4.5V, I_D = 7.5A$	
Forward Transfer Admittance	Y <sub>fs</sub>	-	2.5	-	S	$V_{DS} = 5V, I_{D} = 10A$	
Diode Forward Voltage	$V_{SD}$	-	0.69	1	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	Ciss	-	478.9	-	pF		
Output Capacitance	Coss	1	96.7	-	pF	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	$C_{rss}$	-	61.4	-	pF	1 = 1.0IVID2	
Gate Resistance	$R_g$	0.4	1.1	1.6	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	$Q_{g}$	-	5.0	8	nC	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 10A	
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_{g}$	-	10.5	17	nC		
Gate-Source Charge	$Q_{gs}$	-	1.8	-	nC		
Gate-Drain Charge	$Q_{gd}$	-	1.6	-	nC		
Turn-On Delay Time	t <sub>D(on)</sub>	-	2.9	-	ns	$V_{GS} = 10V, V_{DS} = 15V,$ $R_{G} = 3\Omega, R_{L} = 1.5\Omega$	
Turn-On Rise Time	t <sub>r</sub>	-	7.9	-	ns		
Turn-Off Delay Time	t <sub>D(off)</sub>	-	14.6	-	ns		
Turn-Off Fall Time	t <sub>f</sub>	-	3.1	-	ns		

Notes:

- 6. Short duration pulse test used to minimize self-heating effect.
- 7. Guaranteed by design. Not subject to production testing.





T<sub>A</sub> = 150°C T<sub>A</sub> = 125°C

T<sub>A</sub> = 85°C

 $T_A = 25^{\circ}C$ 

 $T_A = -55$ °C

25

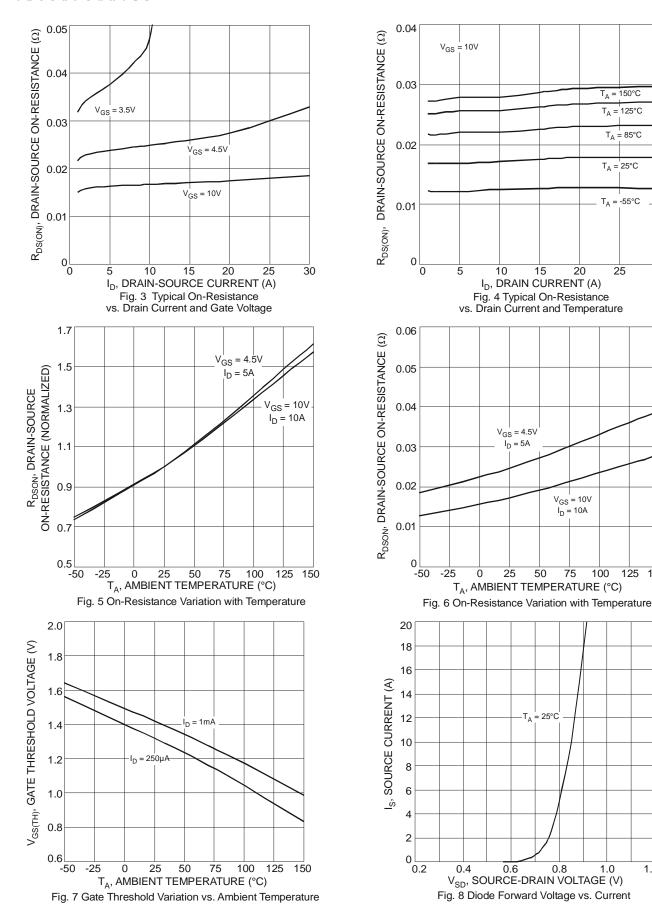
125 150

100

30

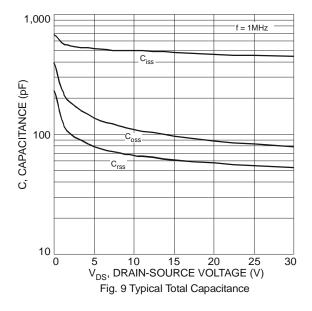
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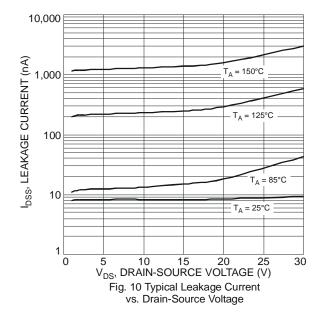


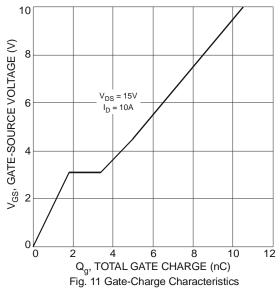


1.2









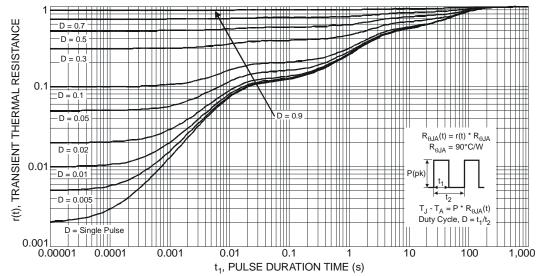


Fig. 12 Transient Thermal Response

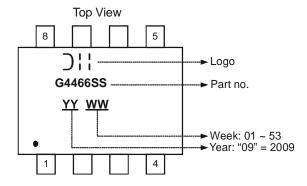


## Ordering Information (Note 8)

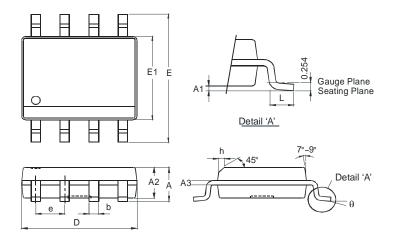
Part Number	Case	Packaging
DMG4466SSSL-13	SO-8	2500 / Tape & Reel

Notes: 8. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

## **Marking Information**

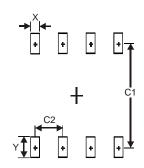


## **Package Outline Dimensions**



SO-8				
Dim	Min	Max		
Α	-	1.75		
<b>A</b> 1	0.10	0.20		
A2	1.30	1.50		
А3	0.15	0.25		
þ	0.3	0.5		
D	4.85	4.95		
Е	5.90	6.10		
E1	3.85	3.95		
е	1.27 Typ			
h	-	0.35		
٦	0.62	0.82		
θ	0°	8°		
All Dimensions in mm				

# Suggested Pad Layout



Dimensions	Value (in mm)
Х	0.60
Y	1.55
C1	5.4
C2	1.27



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